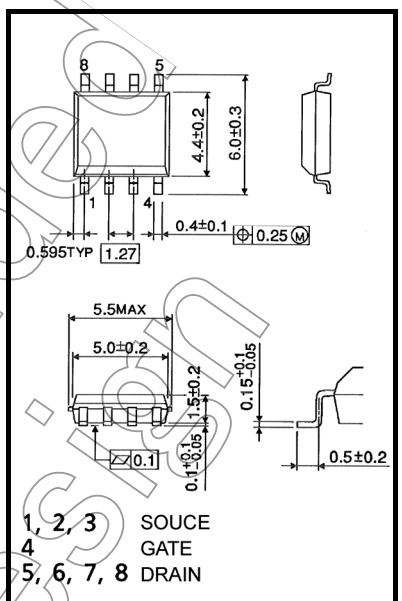
TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (Ultra-High-Speed U−MOS III)

TPC8022-H

High-Efficiency DC/DC Converter Applications
Notebook PC Applications
Portable-Equipment Applications
CCFL Inverter Applications

- Small footprint due to a small and thin package
- High speed switching
- Small gate charge: Q_{SW} = 3.5 nC (typ.)
- Low drain−source ON-resistance: $R_{DS\ (ON)}$ = 22 mΩ (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 15 S (typ.)
- Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 40 V)
- Enhancement mode: V_{th} = 1.1 to 2.3 V (V_{DS} = 10 V, I_D = 1 mA)

Unit: mm



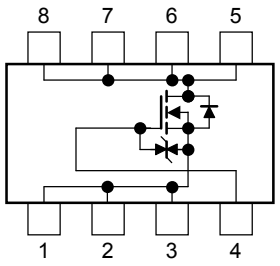
JEDEC	—
JEITA	—
TOSHIBA	2-6J1B

Weight: 0.085 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic			Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	40	V
Drain-gate voltage (R_{GS} = 20 kΩ)			V_{DGR}	40	V
Gate-source voltage			V_{GSS}	±20	V
Drain current	D C	(Note 1)	I_D	7.5	A
	Pulse	(Note 1)	I_{DP}	30	
Drain power dissipation (t = 10 s)		(Note 2a)	P_D	1.9	W
Drain power dissipation (t = 10 s)		(Note 2b)	P_D	1.0	W
Single-pulse avalanche energy		(Note 3)	E_{AS}	26	mJ
Avalanche current			I_{AR}	7.5	A
Repetitive avalanche energy Single-device value at dual operation		(Note 2a, 4)	E_{AR}	0.08	mJ
Channel temperature			T_{ch}	150	°C
Storage temperature range			T_{stg}	−55 to 150	°C

Circuit Configuration



Note: For Notes 1 to 4, refer to the next page.

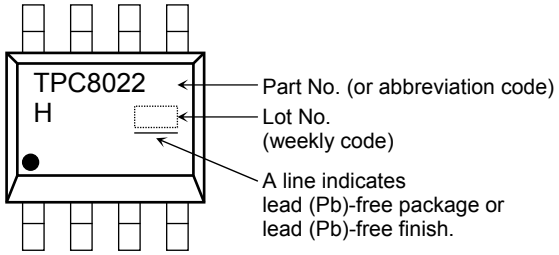
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th\ (ch\text{-}a)}$	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th\ (ch\text{-}a)}$	125	

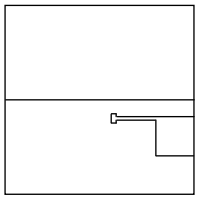
Marking (Note 5)



Note 1: The channel temperature should not exceed 150°C during use.

Note 2:

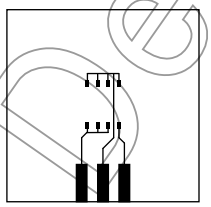
a) Device mounted on a glass-epoxy board (a)



FR-4
25.4 × 25.4 × 0.8
(Unit : mm)

(a)

b) Device mounted on a glass-epoxy board (b)



FR-4
25.4 × 25.4 × 0.8
(Unit : mm)

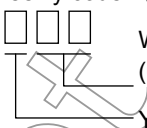
(b)

Note 3: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 0.5 mH, R_G = 25 Ω, I_{AR} = 7.5 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: • on the lower left of the marking indicates Pin 1.

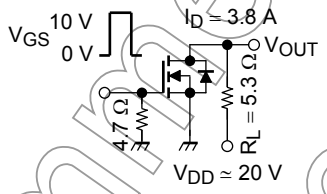
* Weekly code: (Three digits)



Week of manufacture
(01 for first week of year, continuing up to 52 or 53)

Year of manufacture
(The last digit of the calendar year)

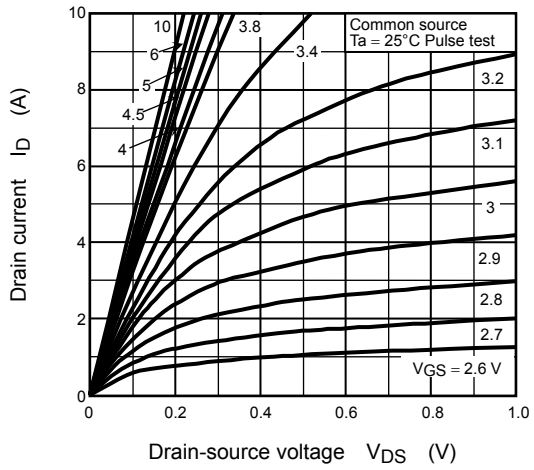
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	—	—	±10	μA
Drain cutoff current		I_{DSS}	V_{DS} = 40 V, V_{GS} = 0 V	—	—	10	μA
Drain−source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	40	—	—	V
		$V_{(BR)\ DSX}$	I_D = 10 mA, V_{GS} = −20 V	25	—	—	
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	1.1	—	2.3	V
Drain−source ON-resistance		$R_{DS\ (ON)}$	V_{GS} = 4.5 V, I_D = 3.8 A	—	27	35	mΩ
		$R_{DS\ (ON)}$	V_{GS} = 10 V, I_D = 3.8 A	—	22	27	
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 3.8 A	7.5	15	—	S
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	650	—	pF
Reverse transfer capacitance		C_{rss}		—	55	—	
Output capacitance		C_{oss}		—	240	—	
Switching time	Rise time	tr		—	3	—	ns
	Turn−on time	t_{on}		—	9	—	
	Fall time	t_f		—	2	—	
	Turn−off time	t_{off}		—	18	—	
Total gate charge (gate−source plus gate−drain)		Q_g	V_{DD} ≈ 32 V, V_{GS} = 10 V, I_D = 7.5 A	—	11	—	nC
			V_{DD} ≈ 32 V, V_{GS} = 5 V, I_D = 7.5 A	—	6.2	—	
Gate−source charge		Q_{gs1}	V_{DD} ≈ 32 V, V_{GS} = 10 V, I_D = 7.5 A	—	2.1	—	
Gate−drain (“Miller”) charge		Q_{gd}		—	2.7	—	
Gate switching charge		Q_{sw}		—	3.5	—	

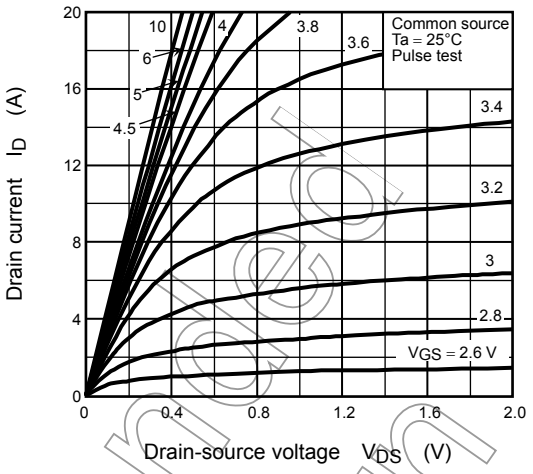
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	30	A
Forward voltage (diode)		V_{DSF}	I_{DR} = 7.5 A, V_{GS} = 0 V	—	—	−1.2	V

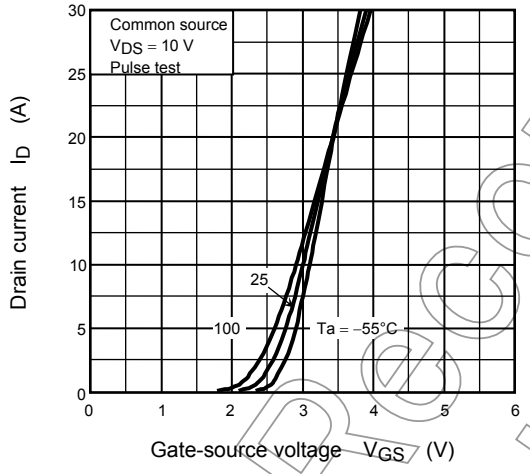
$I_D - V_{DS}$



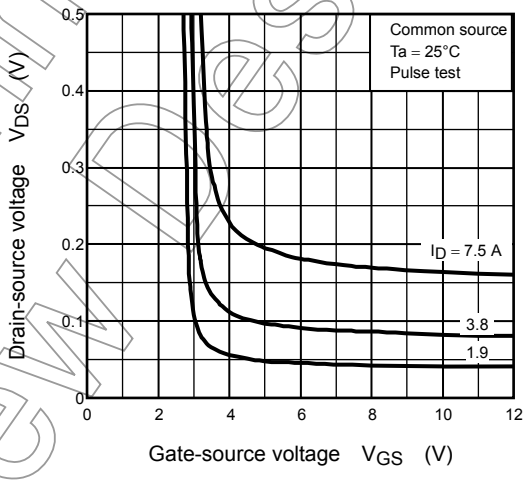
$I_D - V_{DS}$



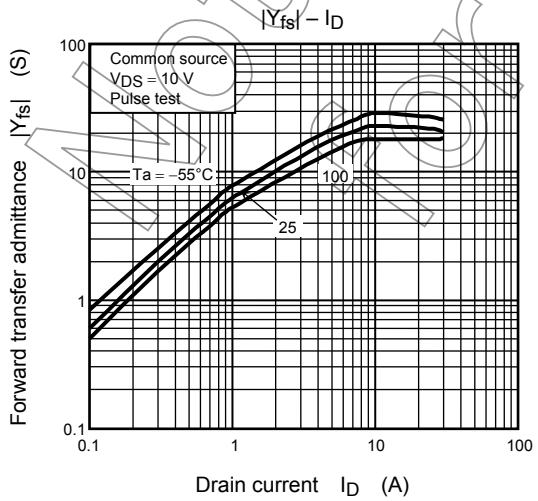
$I_D - V_{GS}$



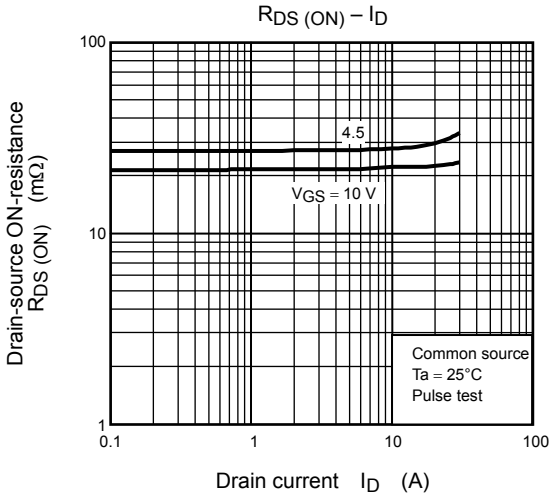
$V_{DS} - V_{GS}$



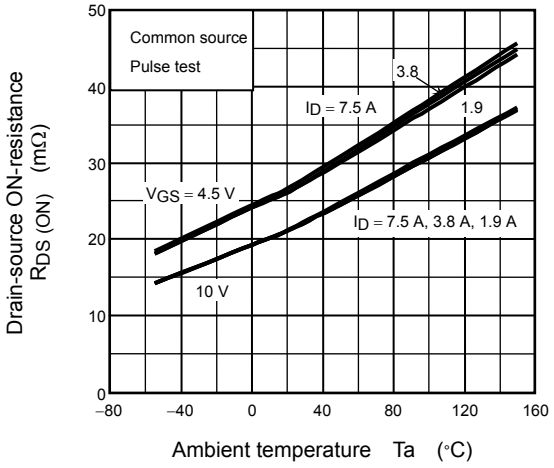
$|Y_{fs}| - I_D$



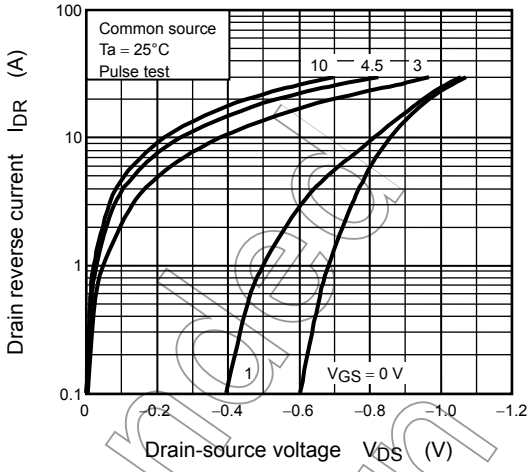
$R_{DS\ (ON)} - I_D$



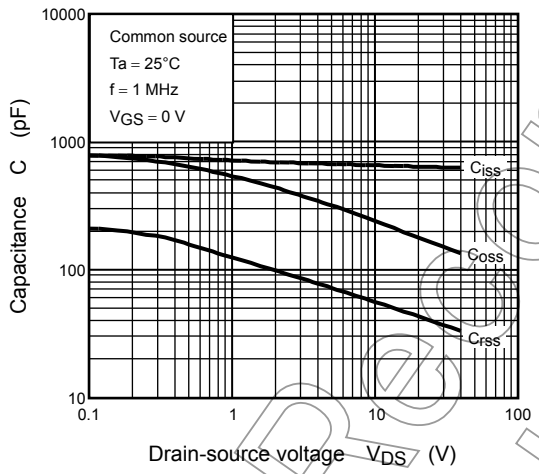
$R_{DS\ (ON)}$ – Ta



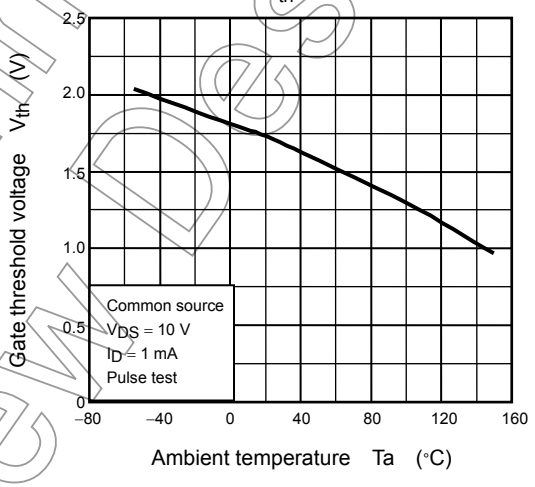
I_{DR} – V_{DS}



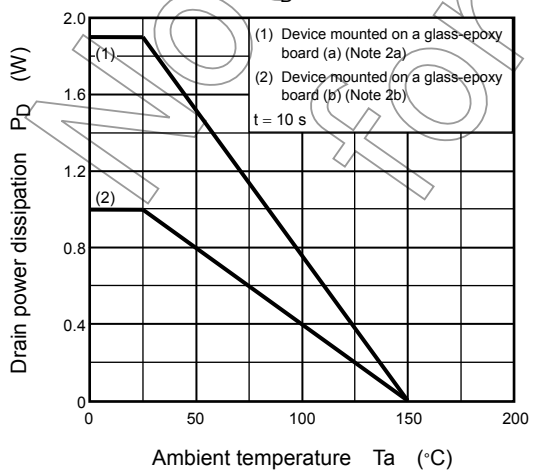
Capacitance – V_{DS}



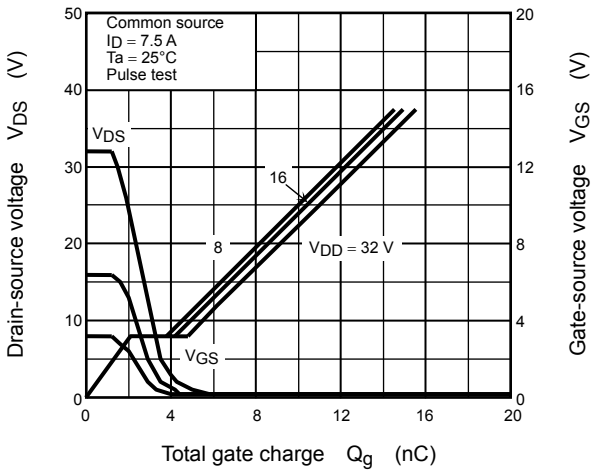
V_{th} – Ta

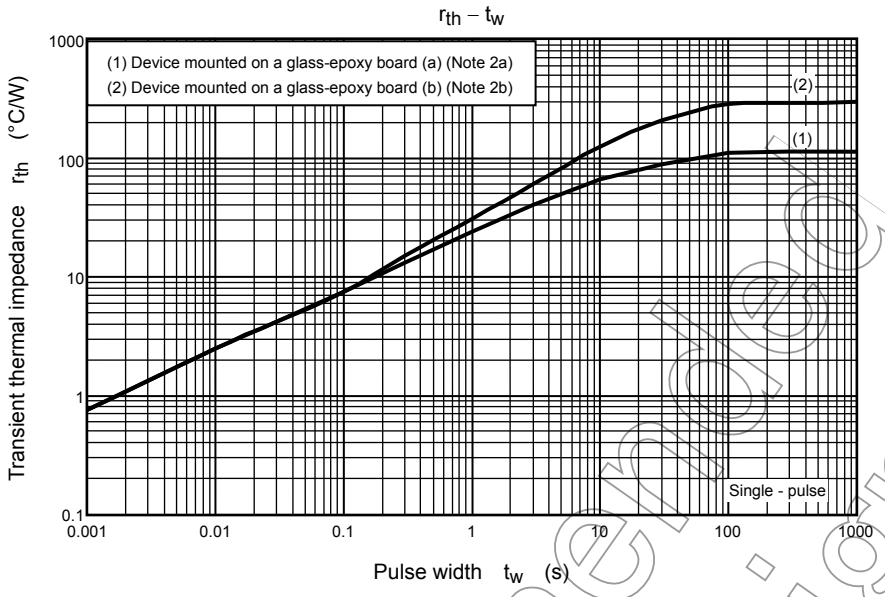


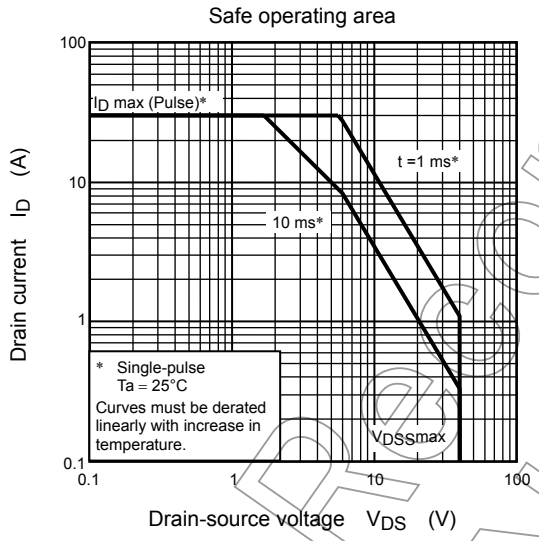
P_D – Ta



Dynamic input/output characteristics







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